

REMARKS

Claims 31, 32, 34-50, and 54-84 are pending in the application with claims 31, 34, 35, and 36 amended herein, claims 33 and 51-53 canceled herein, and new claims 54-84 added herein. Applicants assert that all of the currently pending claims are supported by the specification. Applicants request consideration of the currently pending claims.

Respectfully submitted,

Dated: 29 Jul 2002

By: _____

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TECHNOLOGY CENTER 2800

Application Serial No. 10/053,201
Filing Date January 15, 2002
Inventor Harry Rosenberg, et al.
Assignee Honeywell International Inc.
Group Art Unit 2818
Examiner P. Dang
Attorney's Docket No. 34593-CON1
Title: Tantalum Sputtering Target and Method of Manufacture

VERSION WITH MARKINGS TO SHOW CHANGES MADE ACCOMPANYING
RESPONSE TO DATE OFFICE ACTION

In the Claims

The claims have been amended as follows. Underlines indicate insertions and ~~strikeouts~~ indicate deletions.

31. (Once amended) A layer comprising high purity tantalum, less than about 500 ppm, by weight, total metallic impurities, ~~and less than about 50~~ 20 ppm, by weight, total of tungsten or and molybdenum, and less than 50 ppm, by weight, niobium.

34. (Once amended) ~~The capacitor of claim 33 wherein the high purity tantalum is formed in the capacitor by sputter deposition.~~ The layer of claim 31 comprising less than about 10 ppmw niobium.

35. (Once amended) A sputtering target blank comprising tantalum, less than 500 ppm by weight (ppmw) total metallic impurities, less than ~~or equal to 50~~ 5 ppmw total of molybdenum or and tungsten, and less than about 100 ppmw oxygen, and less than 50 ppmw niobium.

36. (Once amended) The blank of claim 35 comprising less than 5 10 ppmw ~~total of~~
~~molybdenum and tungsten~~ niobium.

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